

Taha Ayari

List of Publications by Year in descending order

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12
papers

313
citations

1163117

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docs citations

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times ranked

533
citing authors

#	ARTICLE	IF	CITATIONS
1	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride—A key enabler of III-nitride flexible optoelectronics. <i>APL Materials</i> , 2021, 9, .	5.1	9
2	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. <i>Scientific Reports</i> , 2020, 10, 21709.	3.3	12
3	Heterogeneous Integration: Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications (<i>Adv. Mater. Technol.</i>) <i>Tj ETOP</i> 1 0.784314 rg	1.0	1
4	Light-Emitting Diodes: Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride (<i>Adv. Mater. Interfaces</i> 16/2019). <i>Advanced Materials Interfaces</i> , 2019, 6, 1970102.	3.7	1
5	Nanopyramid-based absorber to boost the efficiency of InGaN solar cells. <i>Solar Energy</i> , 2019, 190, 93-103.	6.1	7
6	Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride. <i>Advanced Materials Interfaces</i> , 2019, 6, 1900207.	3.7	12
7	Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications. <i>Advanced Materials Technologies</i> , 2019, 4, 1900164.	5.8	10
8	MOVPE van der Waals epitaxial growth of AlGaIn/AlGaIn multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. <i>Journal of Crystal Growth</i> , 2019, 507, 352-356.	1.5	8
9	Heterogeneous Integration of Thin-Film InGaIn-Based Solar Cells on Foreign Substrates with Enhanced Performance. <i>ACS Photonics</i> , 2018, 5, 3003-3008.	6.6	20
10	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. <i>Scientific Reports</i> , 2017, 7, 15212.	3.3	54
11	Wafer-scale controlled exfoliation of metal organic vapor phase epitaxy grown InGaIn/GaN multi quantum well structures using low-tack two-dimensional layered h-BN. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	74
12	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. <i>Crystal Growth and Design</i> , 2016, 16, 3409-3415.	3.0	106